

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Saxler et al.

U.S. Patent No.: 7,432,142 B2

Application No.: 10/849,617

Issued: October 7, 2008

Filed: May 20, 2004

Confirmation No: 9882

For: METHODS OF FABRICATING NITRIDE-BASED TRANSISTORS HAVING
REGROWN OHMIC CONTACT REGIONS

October 28, 2008

Commissioner for Patents

Attn: Certificate of Correction Branch

P.O. Box 1450

Alexandria, VA 22313-1450

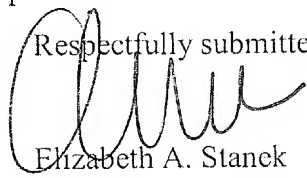
**REQUEST FOR ENTRY OF CERTIFICATE OF CORRECTION UNDER
No. 35 U.S.C §254 AND 37 C.F.R. §1.322**

Sir:

The Assignee of record for the above-referenced patent hereby requests, pursuant to 35 U.S.C §254 and 37 C.F.R. §1.322, that a Certificate of Correction be issued. This request is made in order to correct the mistakes incurred through the fault of the U.S. Patent and Trademark Office. The mistakes appearing in the patent are set forth with corrections on the Certificate of Correction enclosed herewith. The Assignee further directs the Commissioner's attention to the attached IDS considered on 04/05/2006.

No fee is believed due. However, the Commissioner is authorized to charge any deficiency or credit any overpayment to Deposit Account No. 50-0220.

Respectfully submitted,



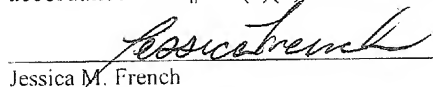
Elizabeth A. Stanek

Registration No. 48,568

Myers Bigel Sibley & Sajovec, P.A.
P. O. Box 37428, Raleigh, NC 27627
Telephone: (919) 854-1400
Facsimile: (919) 854-1401
Customer No. 20792

CERTIFICATION OF ELECTRONIC TRANSMISSION

I hereby certify that this correspondence is being transmitted via the Office electronic filing system in accordance with § 1.6(a)(4) to the U.S. Patent and Trademark Office on October 28, 2008.



Jessica M. French

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

Page 1 of 1

PATENT NO. : 7,432,142 B2
APPLICATION NO.: 10/849,617
DATED : October 7, 2008
INVENTOR(S) : Saxler et al.

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Item 56, References Cited, Foreign Patent Documents, Page 2:
Please correct "JP 2001230401 A 8/2001"
To read -- JP 2001230407 A 8/2001 --

In the Claims:

Column 14, Claim 5, Line 40: Please correct "baffler"
To read -- barrier --

Column 14, Claim 5, Line 46: Please correct "baffler"
To read -- barrier --

Column 15, Claim 16, Line 52: Please correct "baffler"
To read -- barrier --

MAILING ADDRESS OF SENDER:
Myers, Bigel, Sibley & Sajovec
P.O. Box 37428
Raleigh, NC 27627

Substitute form 1449A/PTO			Co. <u>te if Known</u>	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Application Number	10/849,617
			Filing Date	May 20, 2004
			First Named Inventor	Saxler
			Group Art Unit	2841
			Examiner Name	Te-Be Assigned
Sheet A2	of	A3	Attorney Docket Number	5308-392

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No.	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T
		Office	Number	Kind Code (if known)			
KBD	44.	PCT	WO 03/049193	A1	Cree, Inc.	06-12-2003	
	45.	JP	2002016087	A	NEC Corp	01-18-2002	Abstract
	46.	JP	2001230407	A	Matsushita Electric Industrial Co. Ltd.	08-24-2001	Abstract
	47.	PCT	WO 01/57929	A1	Cree Lighting Company	08-09-2001	
	48.	JP	10-050982		Nippon Telegraph & Telephone Corp.	02-20-1998	Abstract
	49.	PCT	WO 93/23877	A1	Massachusetts Institute of Technology	11-25-1993	
✓	50.	EP	0 563 847	A2	Matsushita Electric Industrial Co., Ltd.	10-06-1993	

OTHER NON PATENT LITERATURE DOCUMENTS						
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published				T
KBD	51.	Asbeck et al. "Piezoelectric charge densities in AlGaIn/GaN HFETs," <i>Electronics Letters</i> . Vol. 33, No. 14, pp. 1230-1231 (1997).				
	52.	Ben-Yaacov et al., "AlGaIn/GaN Current Aperture Vertical Electron Transistors with Regrown Channels," <i>Journal of Applied Physics</i> . Vol. 95, No. 4, pp. 2073-2078 (2004).				
	53.	Breitschadel et al. "Minimization of Leakage Current of Recessed Gate AlGaIn/GaN HEMTs by Optimizing the Dry-Etching Process," <i>Journal of Electronic Materials</i> . Vol. 28, No. 12, pp. 1420-1423 (1999).				
	54.	Burm et al. "Recessed Gate GaN MODFETS," <i>Solid-State Electronics</i> . Vol. 41, No. 2, pp. 247-250 (1997).				
	55.	Burm et al. "Ultra-Low Resistive Ohmic Contacts on n-GaN Using Si Implantation," <i>Applied Physics Letters</i> . Vol. 70, No. 4, 464-66 (1997).				
	56.	Chen et al. "Cl2 reactive ion etching for gate recessing of AlGaIn/GaN field-effect transistors," <i>J. Vac. Sci. Technol. B</i> . Vol. 17, No. 6, pp. 2755-58 (1999).				
	57.	Eastman et al. "GaN materials for high power microwave amplifiers," <i>Mat. Res. Soc. Symp. Proc.</i> Vol. 512 (1998).				
	58.	Eastman et al. "Undoped AlGaIn/GaN HEMTs for Microwave Power Amplification," <i>IEEE Transactions on Electron Devices</i> . Vol. 48, No. 3, pp. 479-85 (March 2001).				
	59.	Egawa et al. "Recessed gate AlGaIn/GaN MODFET on Sapphire Grown by MOCVD," <i>Applied Physics Letters</i> . Vol. 76, No. 1, pp. 121-123 (January 2000).				
	60.	Gaska et al. "High-Temperature Performance of AlGaIn/GaN HFET's on SiC Substrates," <i>IEEE Electron Device Letters</i> . Vol. 18, No. 1, pp. 492-494 (October 1997).				
	61.	Gaska et al. "Electron Transport in AlGaIn/GaN Heterostructures Grown on 6H-SiC Substrates," <i>Applied Physics Letters</i> . Vol. 72, No. 6, pp. 707-709 (February 1998).				
	62.	Gelmont et al. "Monte Carlo simulation of electron transport in gallium nitride," <i>Journal of Applied Physics</i> . Vol. 74, No. 3, pp. 1818-1821 (August 1993).				
	63.	Heikman, et al., "Mass Transport Regrowth of GaN for Ohmic Contacts to AlGaIn/GaN," <i>Applied Physics Letters</i> . Vol. 78, No. 19, pp. 2876				
	64.	Heikman et al. "Polarization Effects in AlGaIn/GaN and GaN/AlGaIn/GaN heterostructures," <i>Journal of Applied Physics</i> . Vol. 93, No. 12, pp. 10114-10118 (June 2003).				
	65.	Heikman et al., "Growth of Fe-Doped Semi-insulating GaN by Metalorganic-Chemical Vapor Deposition," <i>Applied Physics Letters</i> . Vol. 83, No. 1, pp. 439-441 (July 2002).				
	66.	Heikman, Sten J., <i>MOCVD Growth Technologies for Applications in AlGaIn/GaN High Electron Mobility Transistors</i> , Dissertation, University of California—Santa Barbara, September 2002, 190 pages.				
	67.	Karmalkar et al. "Enhancement of Breakdown Voltage in AlGaIn/GaN High Electron Mobility Transistors Using a Field Plate," <i>IEEE Transactions on Electron Devices</i> . Vol. 48, No. 8, pp. 1515-1521 (August 2001).				
	68.	Karmalkar et al. "RESURF AlGaIn/GaN HEMT for High Voltage Power Switching," <i>IEEE Electron Device Letters</i> . Vol. 22, No. 8, pp. 373-375 (August 2001).				
	69.	Kuzmik et al. "Annealing of Schottky contacts deposited on dry etched AlGaIn/GaN," <i>Semiconductor Science and Technology</i> . Vol. 17, No. 11 (November 2002).				
	70.	Neuburger et al. "Design of GaN-based Field Effect Transistor Structures based on Doping Screening of Polarization Fields," <i>WA 1.5, 7th Wide-Gandgap III-Nitride Workshop</i> (March 2002).				
Y	71.	Ping et al. "DC and Microwave Performance of High-Current AlGaIn/GaN Heterostructure Field Effect Transistors Grown on p-Type SiC Substrates," <i>IEEE Electron Device Letters</i> . Vol. 19, No. 2, pp. 54-56 (February 1998).				

Examiner Signature		Date Considered	4/5/2006
--------------------	---	-----------------	----------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.